

H7N1004FN

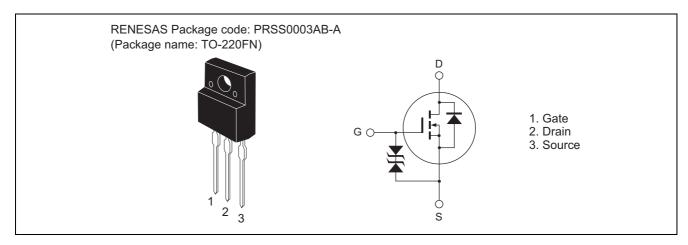
Silicon N-Channel MOSFET High-Speed Power Switching

REJ03G1593-0100 Rev.1.00 Oct 23, 2007

Features

- Low on-resistance
- $R_{DS(on)} = 25 \text{ m}\Omega \text{ typ.}$
- www.DataSheet U Low drive current
 - Available for 4.5 V gate drive

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	100	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	25	А
Drain peak current	I _D (pulse) Note1	100	А
Body-drain diode reverse drain current	I _{DR}	25	А
Avalanche current	I _{AP} Note 3	15	А
Avalanche energy	E _{AR} Note 3	22.5	mJ
Channel dissipation	Pch Note 2	25	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at $Tc = 25^{\circ}C$
- 3. Value at Tch = 25°C, Rg \geq 50 Ω

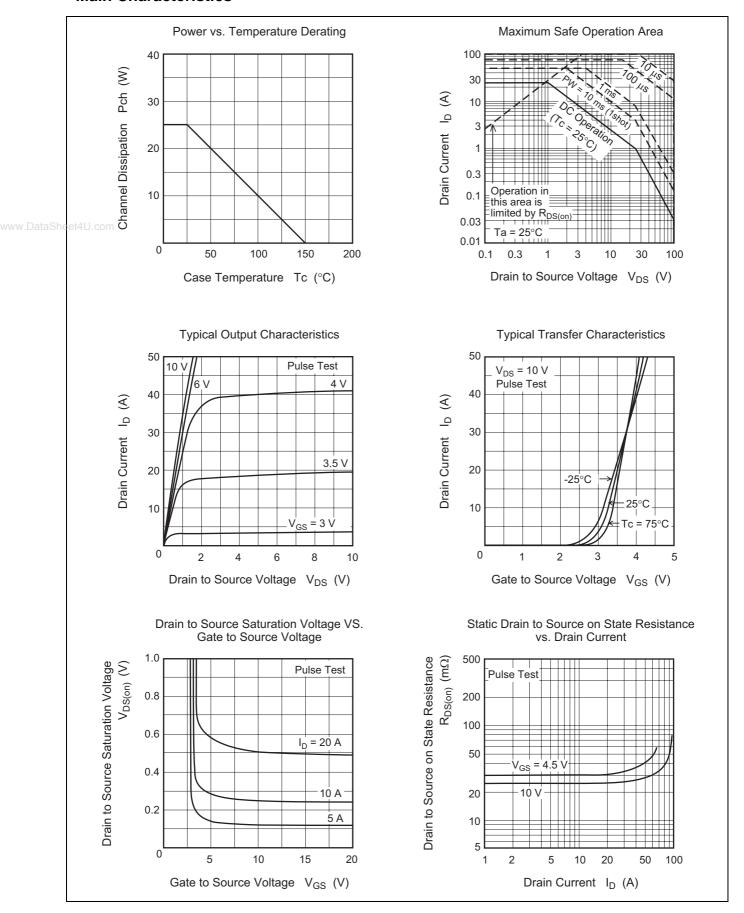
Electrical Characteristics

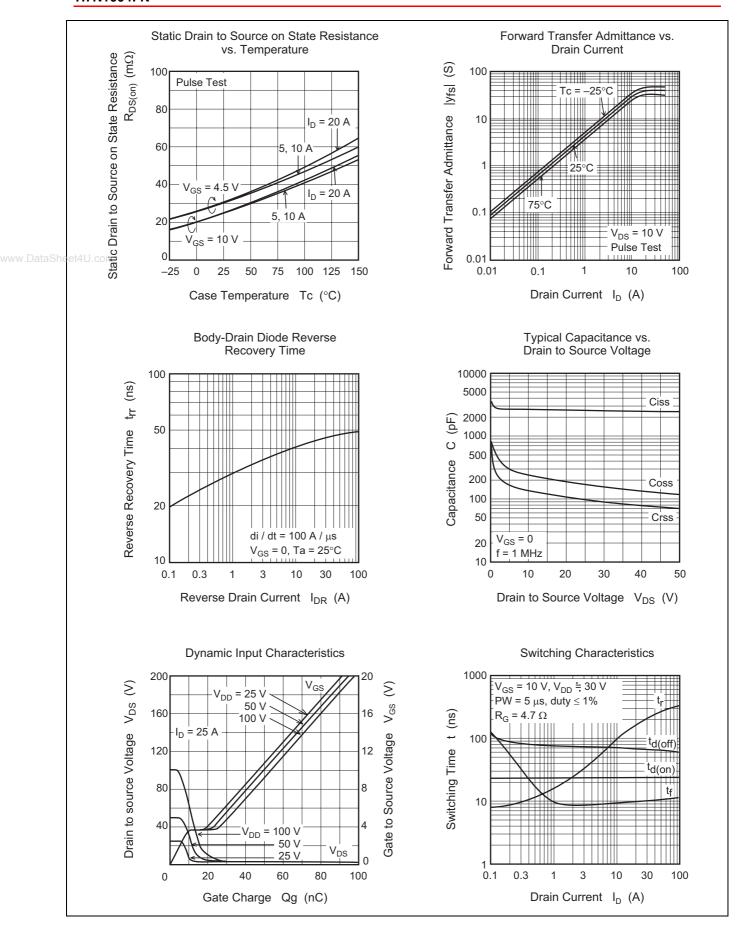
 $(Ta = 25^{\circ}C)$

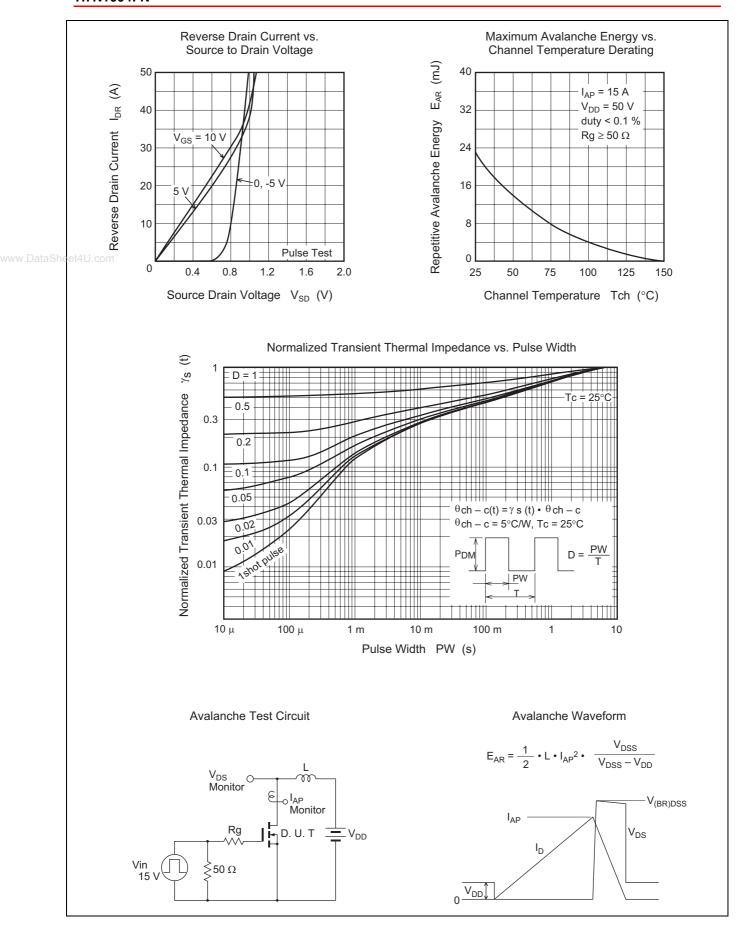
	Item	Symbol	Min	Тур	Max	Unit	Test conditions
	Drain to source breakdown voltage	$V_{(BR)DSS}$	100			V	$I_D = 10 \text{ mA}, V_{GS} = 0$
	Gate to source breakdown voltage	$V_{(BR)GSS}$	±20			V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
	Gate to source leak current	I_{GSS}	_		±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
	Zero gate voltage drain current	I _{DSS}	_		10	μΑ	V _{DS} = 100 V, V _{GS} = 0
	Gate to source cutoff voltage	$V_{GS(off)}$	1.5		2.5	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}^{\text{Note 4}}$
	Static drain to source on state	R _{DS(on)}	_	25	35	mΩ	$I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note 4}}$
	resistance		_	30	45	mΩ	$I_D = 12.5 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note 4}}$
	Forward transfer admittance	y _{fs}	20	35		S	$I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note 4}}$
	Input capacitance	Ciss	_	2800	1	pF	V _{DS} = 10 V
www.DataShe	Output capacitance	Coss	_	240		pF	$V_{GS} = 0$
	Reverse transfer capacitance	Crss	_	140	_	pF	f = 1 MHz
	Total gate charge	Qg	_	50	_	nC	V _{DD} = 50 V
	Gate to source charge	Qgs	_	9	_	nC	V _{GS} = 10 V
	Gate to drain charge	Qgd	_	11	_	nC	I _D = 25 A
	Turn-on delay time	t _{d(on)}	_	23	_	ns	$V_{GS} = 10 \text{ V}, I_D = 12.5 \text{ A}$
	Rise time	t _r	_	110	_	ns	$R_L = 2.4 \Omega$
	Turn-off delay time	$t_{d(off)}$	_	70	_	ns	$Rg = 4.7 \Omega$
	Fall time	t _f	_	9.5	_	ns	
	Body-drain diode forward voltage	V_{DF}	_	0.89	_	V	I _F = 25 A, V _{GS} = 0
	Body-drain diode reverse recovery	t _{rr}	_	45	_	ns	I _F = 25 A, V _{GS} = 0
	time						$di_F/dt = 100 A/\mu s$

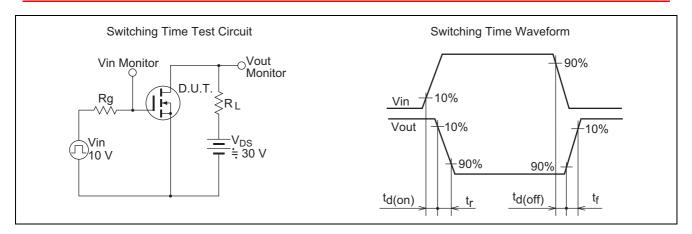
Notes: 4. Pulse test

Main Characteristics



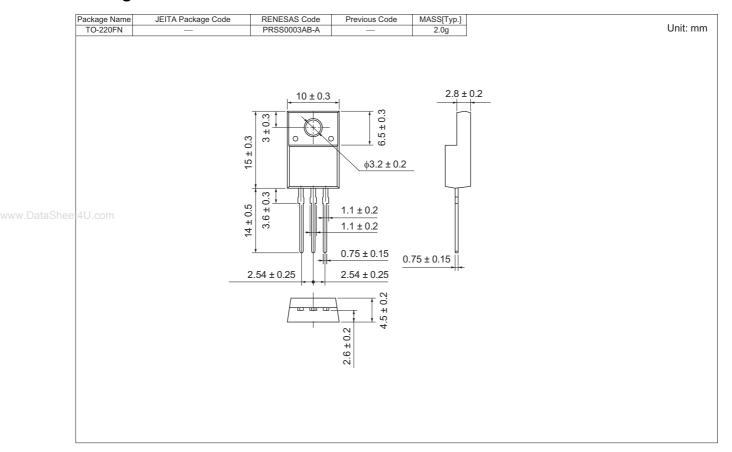






ww.DataSheet4U.com

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
H7N1004FN	50 pcs	Plastic Magazine (Tube)

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

 1. This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warrantes or representations with respect to the accuracy or completeness of the information in this document nor grants any license to any intellectual property girbs to any other rights of representations with respect to the information in this document in this document of the purpose of the respect to the information in this document in the product data, diagrams, charts, programs, algorithms, and application circuit examples.

 3. You should not use the products of the technology described in this document for the purpose of military use. When exporting the products or technology described herein, you should follow the applicable export control laws and regulations, and procedures required by such laws and regulations, and procedures required to change without any place proteins and careful attention to additional and different information to the disclosed by Renesas such as that disclosed through our website, (http://www.renesas.com)

 3. Renesas has a sused reasonable care in compling the information included in this document, but requires a suitable procedure and procedures are required to the procedure of the procedure o



RENESAS SALES OFFICES

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510